

**Anexo B: hoja de datos IR4426, IRG4PC50U.**

International  
**IR** Rectifier

Data Sheet No. PD60177 Rev. E

**IR4426/IR4427/IR4428(S) & (PbF)****DUAL LOW SIDE DRIVER****Features**

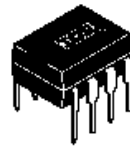
- Gate drive supply range from 6 to 20V
- CMOS Schmitt-triggered inputs
- Matched propagation delay for both channels
- Outputs out of phase with inputs (IR4426)
- Outputs in phase with inputs (IR4427)
- OutputA out of phase with inputA and OutputB in phase with inputB (IR4428)
- Also available LEAD-FREE

**Descriptions**

The IR4426/IR4427/IR4428 (S) is a low voltage, high speed power MOSFET and IGBT driver. Proprietary latch immune CMOS technologies enable ruggedized monolithic construction. Logic inputs are compatible with standard CMOS or LSTTL outputs. The output drivers feature a high pulse current buffer stage designed for minimum driver cross-conduction. Propagation delays between two channels are matched.

**Product Summary**

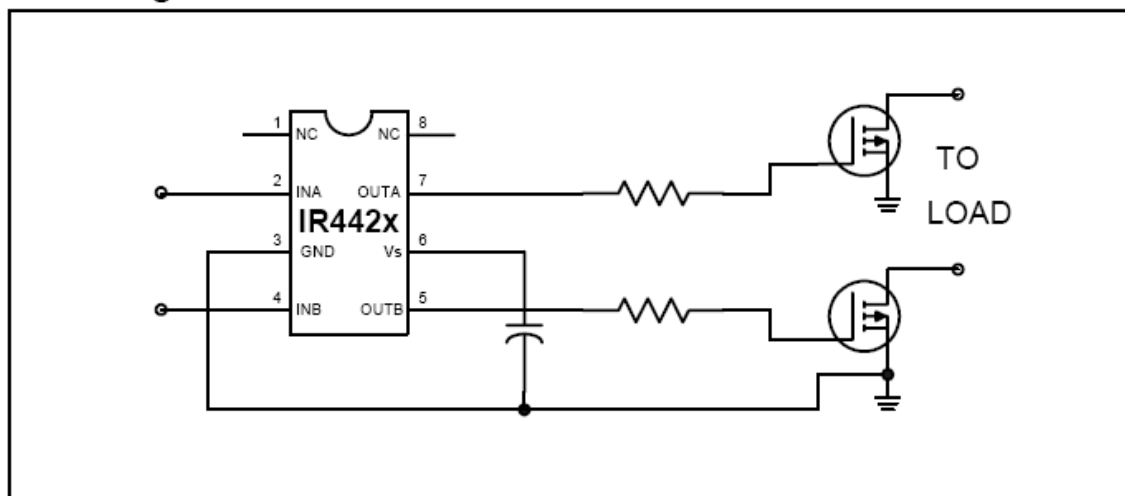
$I_{O+/-}$	1.5A / 1.5A
$V_{OUT}$	6V - 20V
$t_{on/off}$ (typ.)	85 & 65 ns

**Packages**

8 Lead PDIP



8 Lead SOIC

**Block Diagram**

**IR4426/IR4427/IR4428(S) & (PbF)**

## ADVANCE INFORMATION

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Absolute maximum ratings indicate sustained limits beyond which damage to the device may occur. All voltage parameters are absolute voltages referenced to GND. The thermal resistance and power dissipation ratings are measured under board mounted and still air conditions.

Symbol	Definition	Min.	Max.	Units
$V_S$	Fixed supply voltage	-0.3	25	V
$V_O$	Output voltage	-0.3	$V_S + 0.3$	
$V_{IN}$	Logic input voltage	-0.3	$V_S + 0.3$	
$P_D$	Package power dissipation @ $T_A \leq +25^\circ\text{C}$ (8 Lead PDIP)	—	1.0	W
		(8 lead SOIC)	0.625	
$R_{thJA}$	Thermal resistance, junction to ambient (8 lead PDIP)	—	125	$^\circ\text{C/W}$
		(8 lead SOIC)	200	
$T_J$	Junction temperature	—	150	$^\circ\text{C}$
$T_S$	Storage temperature	-55	150	
$T_L$	Lead temperature (soldering, 10 seconds)	—	300	

**Recommended Operating Conditions**

The input/output logic timing diagram is shown in figure 1. For proper operation the device should be used within the recommended conditions. All voltage parameters are absolute voltages referenced to GND.

Symbol	Definition	Min.	Max.	Units
$V_S$	Fixed supply voltage	6	20	V
$V_O$	Output voltage	0	$V_S$	
$V_{IN}$	Logic input voltage	0	$V_S$	
$T_A$	Ambient temperature	-40	125	$^\circ\text{C}$

**DC Electrical Characteristics**

$V_{BIAS} (V_S) = 15\text{V}$ ,  $T_A = 25^\circ\text{C}$  unless otherwise specified. The  $V_{IN}$  and  $I_{IN}$  parameters are referenced to GND and are applicable to input leads: INA and INB. The  $V_O$  and  $I_O$  parameters are referenced to GND and are applicable to the output leads: OUTA and OUTB.

Symbol	Definition	Min.	Typ.	Max.	Units	Test Conditions
$V_{IH}$	Logic "0" input voltage (OUTA=LO, OUTB=LO) (IR4426)	2.7	—	—	V	
	Logic "1" input voltage (OUTA=HI, OUTB=HI) (IR4427)					
	Logic "0" input voltage (OUTA=LO), Logic "1" input voltage (OUTB=HI) (IR4428)					



## IR4426/IR4427/IR4428(S) & (PbF)

### ADVANCE INFORMATION

#### DC Electrical Characteristics cont.

$V_{BIAS}$  ( $V_S$ ) = 15V,  $T_A$  = 25°C unless otherwise specified. The  $V_{IN}$ , and  $I_{IN}$  parameters are referenced to GND and are applicable to input leads: INA and INB. The  $V_O$  and  $I_O$  parameters are referenced to GND and are applicable to the output leads: OUTA and OUTB.

Symbol	Definition	Min.	Typ.	Max.	Units	Test Conditions
$V_{IL}$	Logic "1" input voltage (OUTA=HI, OUTB=HI) (IR4426) Logic "0" input voltage (OUTA=LO, OUTB=LO) (IR4427) Logic "1" input voltage (OUTA=HI), Logic "0" input voltage (OUTB=LO) (IR4428)	—	—	0.8	V	
$V_{OH}$	High level output voltage, $V_{BIAS}-V_O$	—	—	1.2		
$V_{OL}$	Low level output voltage, $V_O$	—	—	0.1		
$I_{IN+}$	Logic "1" input bias current (OUT=HI)	—	5	15	$\mu$ A	$V_{IN} = 0V$ (IR4426) $V_{IN} = V_S$ (IR4427) $V_{INA} = 0V$ (IR4428) $V_{INB} = V_S$ (IR4428)
$I_{IN-}$	Logic "0" input bias current (OUT=LO)	—	-10	-30	$\mu$ A	$V_{IN} = V_S$ (IR4426) $V_{IN} = 0V$ (IR4427) $V_{INA} = V_S$ (IR4428) $V_{INB} = 0V$ (IR4428)
$I_{QS}$	Quiescent $V_S$ supply current	—	100	200		$V_{IN} = 0V$ or $V_S$
$I_{O+}$	Output high short circuit pulsed current	1.5	2.3	—	A	$V_O = 0V, V_{IN} = 0$ (IR4426) $V_O = 0V, V_{IN} = V_S$ (IR4427) $V_O = 0V, V_{INA} = 0$ (IR4428) $V_O = 0V, V_{INB} = V_S$ (IR4428) $PW \leq 10 \mu s$
$I_{O-}$	Output low short circuit pulsed current	1.5	3.3	—	A	$V_O = 15V, V_{IN} = V_S$ (IR4426) $V_O = 15V, V_{IN} = 0$ (IR4427) $V_O = 15V, V_{INA} = V_S$ (IR4428) $V_O = 15V, V_{INB} = 0$ (IR4428) $PW \leq 10 \mu s$

# IR4426/IR4427/IR4428(S) & (PbF)

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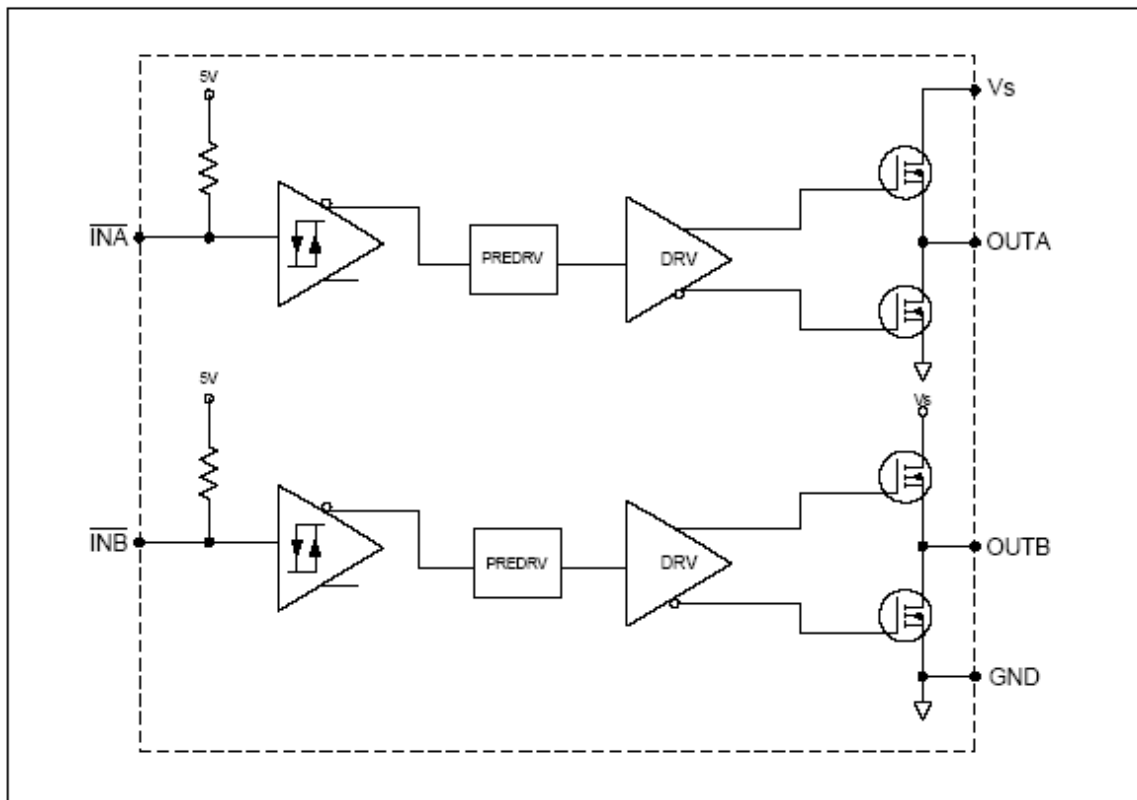
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## AC Electrical Characteristics

$V_{BIAS} (V_S) = 15V$ ,  $C_L = 1000pF$ ,  $T_A = 25^{\circ}C$  unless otherwise specified.

Symbol	Definition	Min.	Typ.	Max.	Units	Test Conditions
<b>Propagation delay characteristics</b>						
$t_{d1}$	Turn-on propagation delay	—	85	160	ns	figure 4
$t_{d2}$	Turn-off propagation delay	—	65	150		
$t_r$	Turn-on rise time	—	15	35		
$t_f$	Turn-off fall time	—	10	25		

## Functional Block Diagram IR4426



**IR4426/IR4427/IR4428(S) & (PbF)**

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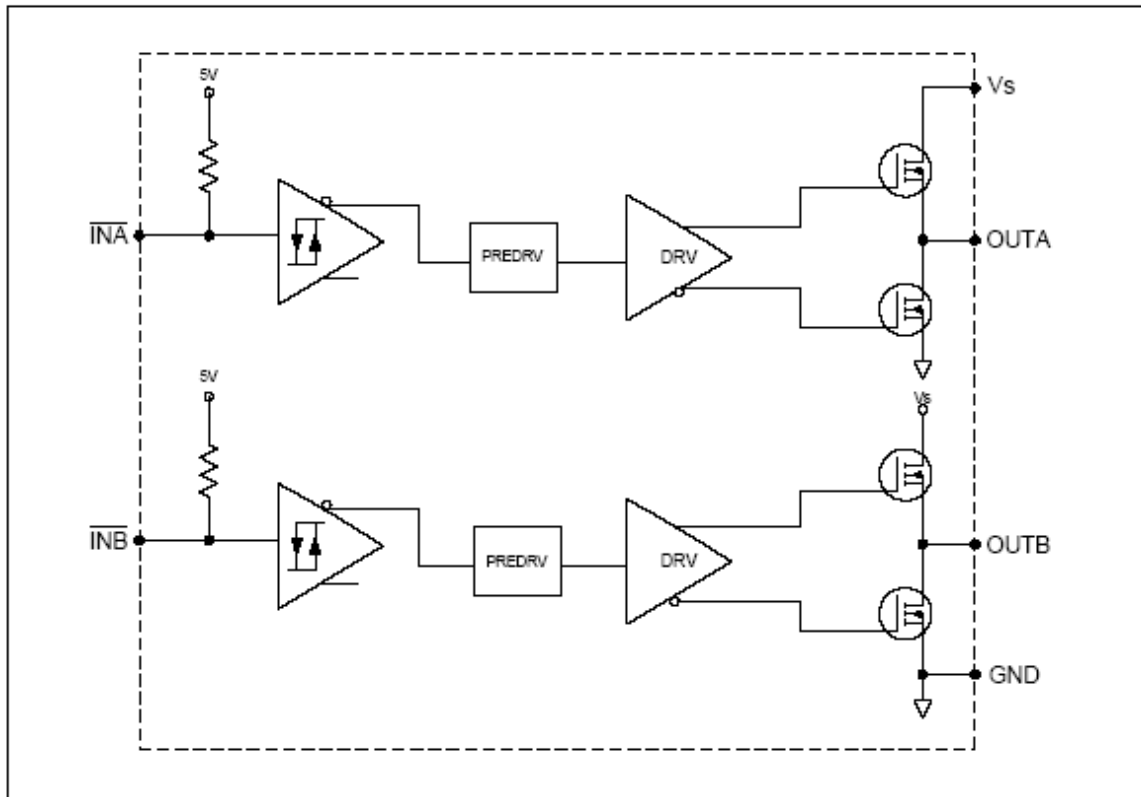
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**AC Electrical Characteristics**

$V_{BIAS} (V_S) = 15V, C_L = 1000pF, T_A = 25^\circ C$  unless otherwise specified.

Symbol	Definition	Min.	Typ.	Max.	Units	Test Conditions
<b>Propagation delay characteristics</b>						
$t_{d1}$	Turn-on propagation delay	—	85	160	ns	figure 4
$t_{d2}$	Turn-off propagation delay	—	65	150		
$t_r$	Turn-on rise time	—	15	35		
$t_f$	Turn-off fall time	—	10	25		

**Functional Block Diagram IR4426**

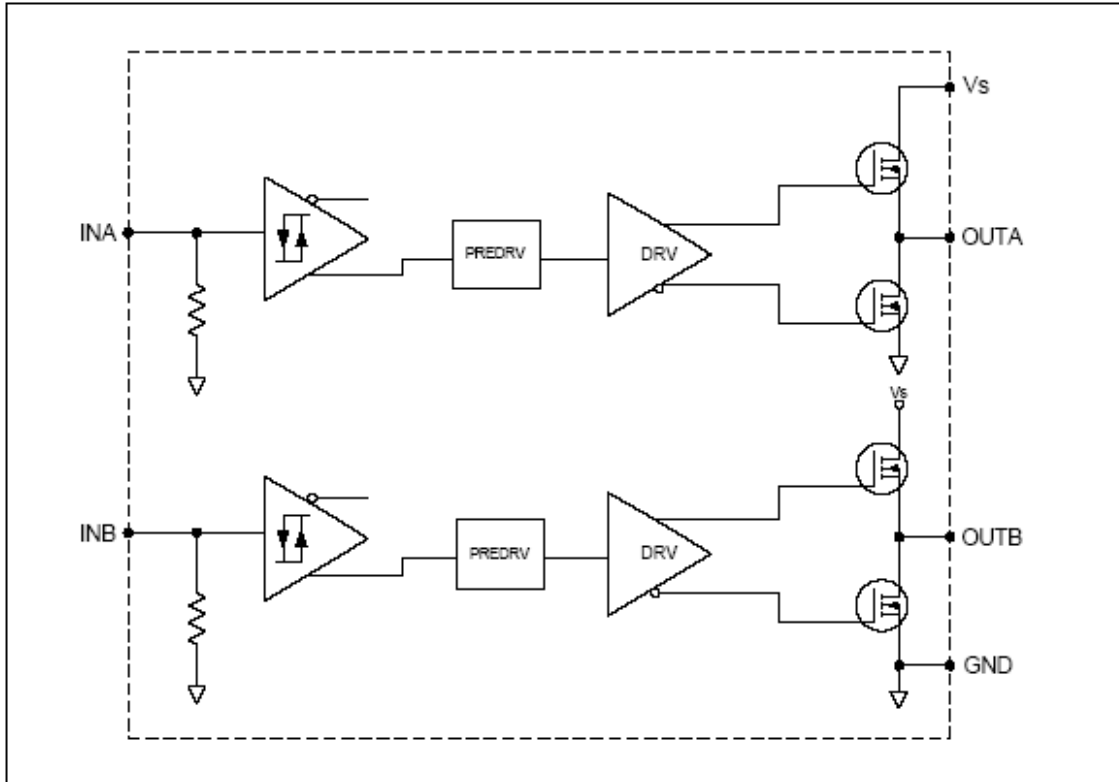


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### IR4426/IR4427/IR4428(S) & (PbF)

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#### Functional Block Diagram IR4427



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PD 91470F

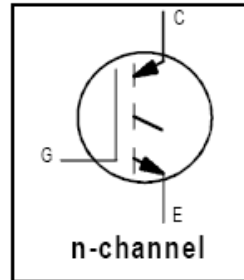
**IRG4PC50U**

INSULATED GATE BIPOLAR TRANSISTOR

UltraFast Speed IGBT

**Features**

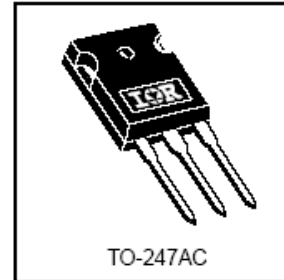
- UltraFast: Optimized for high operating frequencies 8-40 kHz in hard switching, >200 kHz in resonant mode
- Generation 4 IGBT design provides tighter parameter distribution and higher efficiency than Generation 3
- Industry standard TO-247AC package



$V_{CES} = 600V$   
 $V_{CE(on)typ.} = 1.65V$   
 @ $V_{GE} = 15V, I_C = 27A$

**Benefits**

- Generation 4 IGBT's offer highest efficiency available
- IGBT's optimized for specified application conditions
- Designed to be a "drop-in" replacement for equivalent industry-standard Generation 3 IR IGBT's

**Absolute Maximum Ratings**

	Parameter	Max.	Units
$V_{CES}$	Collector-to-Emitter Breakdown Voltage	600	V
$I_C @ T_C = 25^\circ C$	Continuous Collector Current	55	A
$I_C @ T_C = 100^\circ C$	Continuous Collector Current	27	
$I_{CM}$	Pulsed Collector Current ①	220	
$I_{LM}$	Clamped Inductive Load Current ②	220	
$V_{GE}$	Gate-to-Emitter Voltage	$\pm 20$	V
$E_{ARV}$	Reverse Voltage Avalanche Energy ③	20	mJ
$P_D @ T_C = 25^\circ C$	Maximum Power Dissipation	200	W
$P_D @ T_C = 100^\circ C$	Maximum Power Dissipation	78	
$T_J$	Operating Junction and	-55 to + 150	°C
$T_{STG}$	Storage Temperature Range		
	Soldering Temperature, for 10 seconds	300 (0.063 in. (1.6mm from case )	
	Mounting torque, 6-32 or M3 screw.	10 lbf·in (1.1N·m)	

**Thermal Resistance**

	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	----	0.64	°C/W
$R_{\theta CS}$	Case-to-Sink, Flat, Greased Surface	0.24	----	
$R_{\theta JA}$	Junction-to-Ambient, typical socket mount	----	40	
Wt	Weight	6 (0.21)	----	g (oz)

## IRG4PC50U

International  
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	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)CES}$	Collector-to-Emitter Breakdown Voltage	600	----	----	V	$V_{GE} = 0V, I_C = 250\mu A$
$V_{(BR)ECS}$	Emitter-to-Collector Breakdown Voltage ①	18	----	----	V	$V_{GE} = 0V, I_C = 1.0A$
$\Delta V_{(BR)CES}/\Delta T_J$	Temperature Coeff. of Breakdown Voltage	----	0.60	----	$V/^\circ\text{C}$	$V_{GE} = 0V, I_C = 1.0mA$
$V_{CE(ON)}$	Collector-to-Emitter Saturation Voltage	----	1.65	2.0	V	$I_C = 27A$ $V_{GE} = 15V$ See Fig.2, 5
		----	2.0	----		
		----	1.6	----		
$V_{GE(th)}$	Gate Threshold Voltage	3.0	----	6.0		$V_{CE} = V_{GE}, I_C = 250\mu A$
$\Delta V_{GE(th)}/\Delta T_J$	Temperature Coeff. of Threshold Voltage	----	-13	----	$mV/^\circ\text{C}$	$V_{CE} = V_{GE}, I_C = 250\mu A$
$g_{fe}$	Forward Transconductance ②	16	24	----	S	$V_{CE} \geq 15V, I_C = 27A$
$I_{CES}$	Zero Gate Voltage Collector Current	----	----	250	$\mu A$	$V_{GE} = 0V, V_{CE} = 600V$
		----	----	2.0		$V_{GE} = 0V, V_{CE} = 10V, T_J = 25^\circ\text{C}$
		----	----	5000		$V_{GE} = 0V, V_{CE} = 600V, T_J = 150^\circ\text{C}$
$I_{GES}$	Gate-to-Emitter Leakage Current	----	----	$\pm 100$	nA	$V_{GE} = \pm 20V$

Switching Characteristics @  $T_J = 25^\circ\text{C}$  (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$Q_g$	Total Gate Charge (turn-on)	----	180	270	nC	$I_C = 27A$ $V_{CC} = 400V$ $V_{GE} = 15V$ See Fig. 8
$Q_{ge}$	Gate - Emitter Charge (turn-on)	----	25	38		
$Q_{gc}$	Gate - Collector Charge (turn-on)	----	61	90		
$t_{d(on)}$	Turn-On Delay Time	----	32	----	ns	$T_J = 25^\circ\text{C}$ $I_C = 27A, V_{CC} = 480V$ $V_{GE} = 15V, R_G = 5.0\Omega$ Energy losses include "tail" See Fig. 10, 11, 13, 14
$t_r$	Rise Time	----	20	----		
$t_{d(off)}$	Turn-Off Delay Time	----	170	260		
$t_f$	Fall Time	----	88	130		
$E_{on}$	Turn-On Switching Loss	----	0.12	----		
$E_{off}$	Turn-Off Switching Loss	----	0.54	----	mJ	See Fig. 10, 11, 13, 14
$E_{\Sigma}$	Total Switching Loss	----	0.66	0.9		
$t_{d(on)}$	Turn-On Delay Time	----	31	----	ns	$T_J = 150^\circ\text{C}$ , $I_C = 27A, V_{CC} = 480V$ $V_{GE} = 15V, R_G = 5.0\Omega$ Energy losses include "tail" See Fig. 13, 14
$t_r$	Rise Time	----	23	----		
$t_{d(off)}$	Turn-Off Delay Time	----	230	----		
$t_f$	Fall Time	----	120	----		
$E_{\Sigma}$	Total Switching Loss	----	1.6	----		
$L_E$	Internal Emitter Inductance	----	13	----	nH	Measured 5mm from package
$C_{ies}$	Input Capacitance	----	4000	----	pF	$V_{GE} = 0V$ $V_{CC} = 30V$ $f = 1.0MHz$ See Fig. 7
$C_{oes}$	Output Capacitance	----	250	----		
$C_{res}$	Reverse Transfer Capacitance	----	52	----		

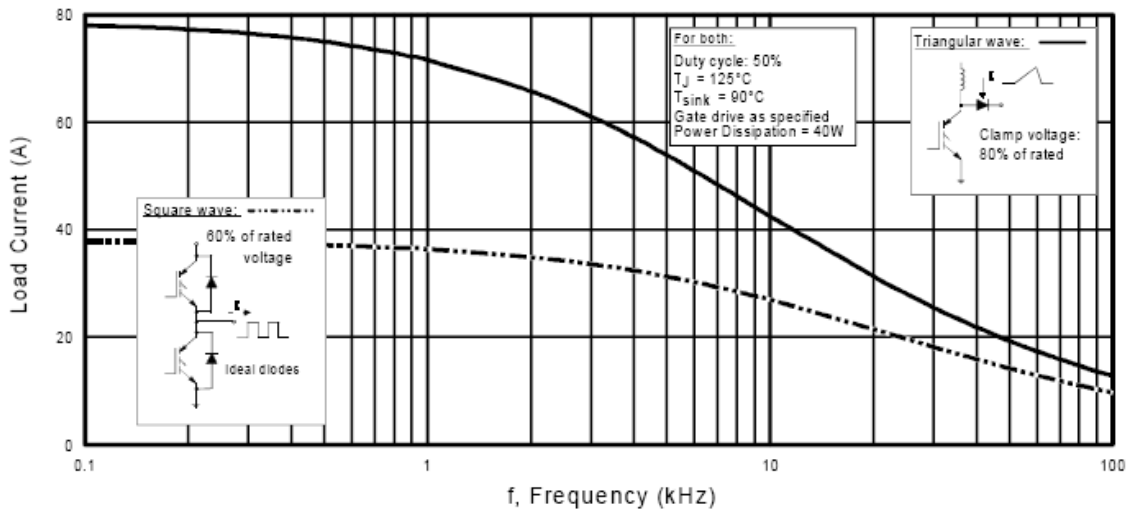
## Notes:

- ① Repetitive rating;  $V_{GE} = 20V$ , pulse width limited by max. junction temperature. ( See fig. 13b )
- ②  $V_{CC} = 80\%(V_{CES})$ ,  $V_{GE} = 20V$ ,  $L = 10\mu H$ ,  $R_G = 5.0\Omega$ , (See fig. 13a)
- ③ Repetitive rating; pulse width limited by maximum junction temperature.
- ④ Pulse width  $\leq 80\mu s$ ; duty factor  $\leq 0.1\%$ .
- ⑤ Pulse width  $5.0\mu s$ , single shot.

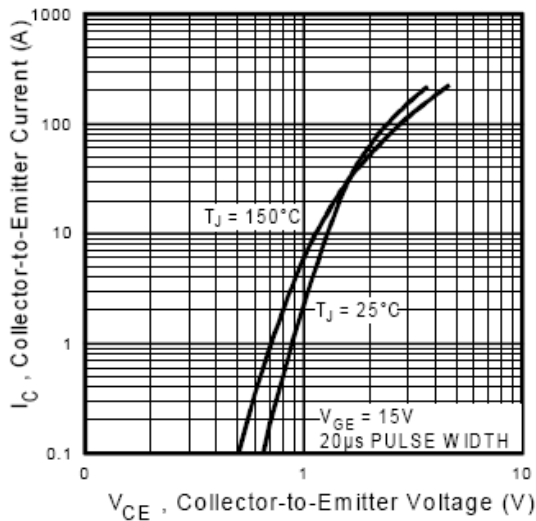


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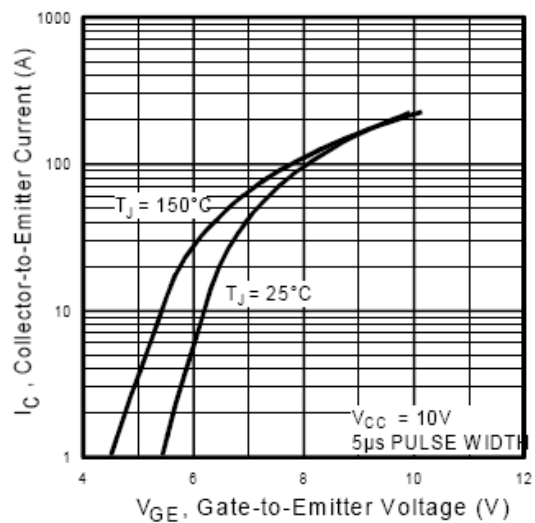
**IRG4PC50U**



**Fig. 1** - Typical Load Current vs. Frequency  
(For square wave,  $I = I_{\text{RMS}}$  of fundamental; for triangular wave,  $I = I_{\text{PK}}$ )



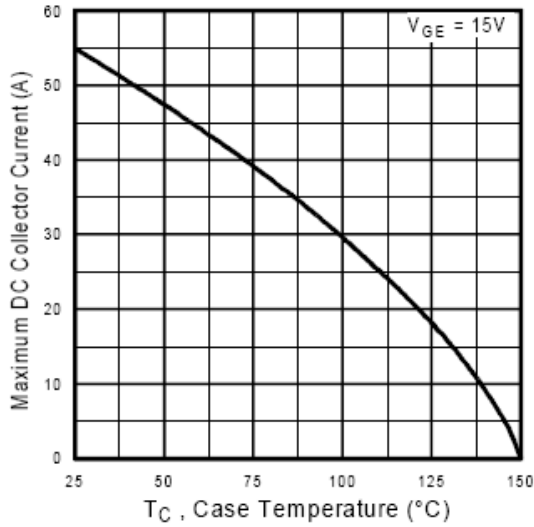
**Fig. 2** - Typical Output Characteristics



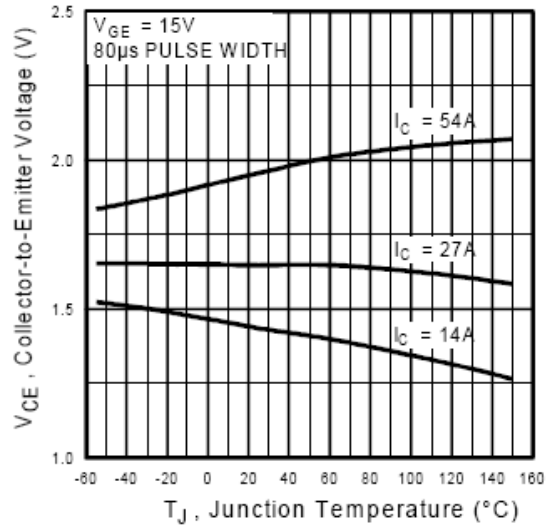
**Fig. 3** - Typical Transfer Characteristics

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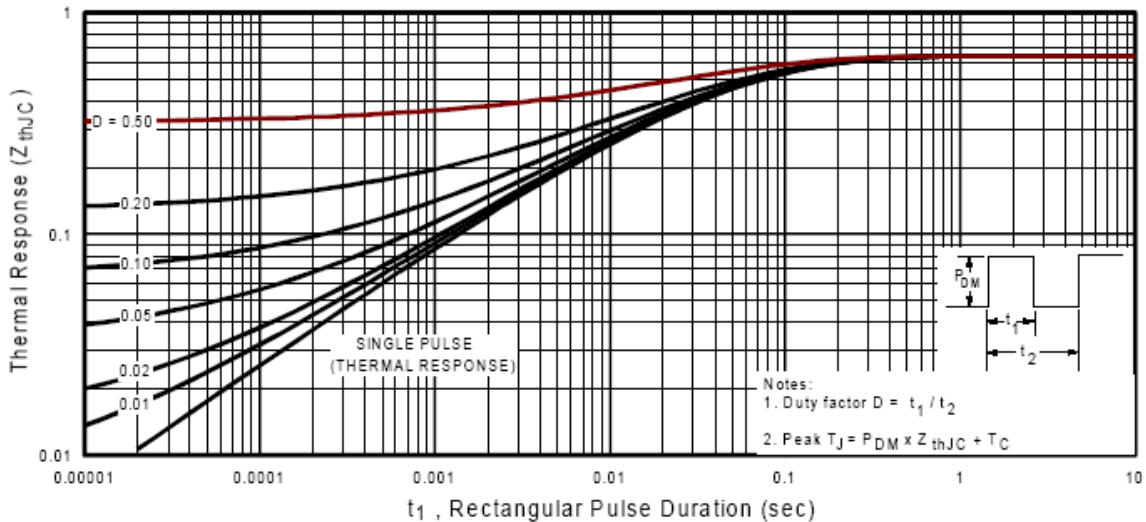
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**Fig. 4** - Maximum Collector Current vs. Case Temperature



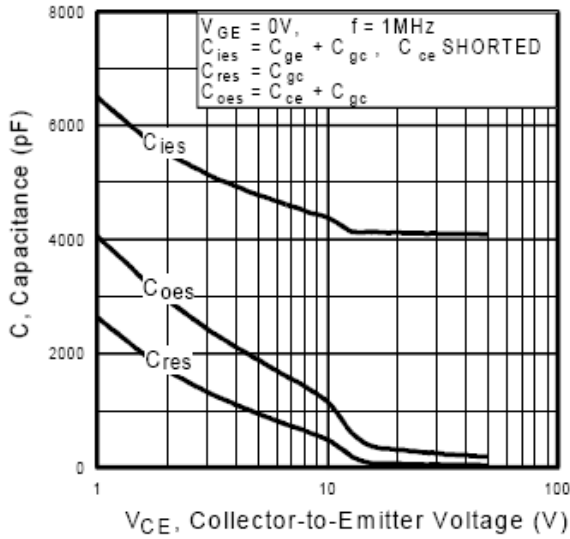
**Fig. 5** - Collector-to-Emitter Voltage vs. Junction Temperature



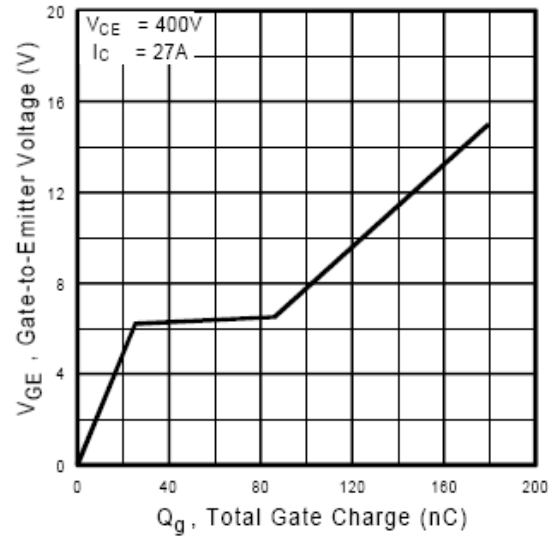
**Fig. 6** - Maximum Effective Transient Thermal Impedance, Junction-to-Case

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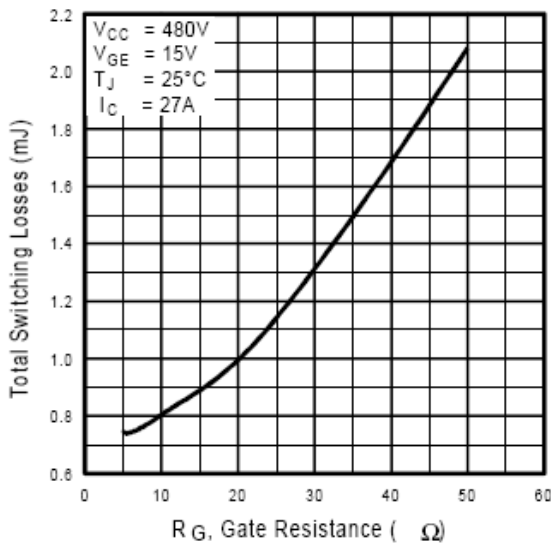
**IRG4PC50U**



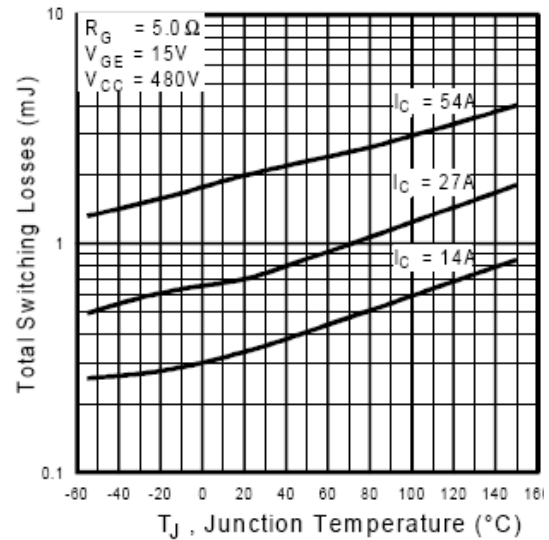
**Fig. 7** - Typical Capacitance vs. Collector-to-Emitter Voltage



**Fig. 8** - Typical Gate Charge vs. Gate-to-Emitter Voltage



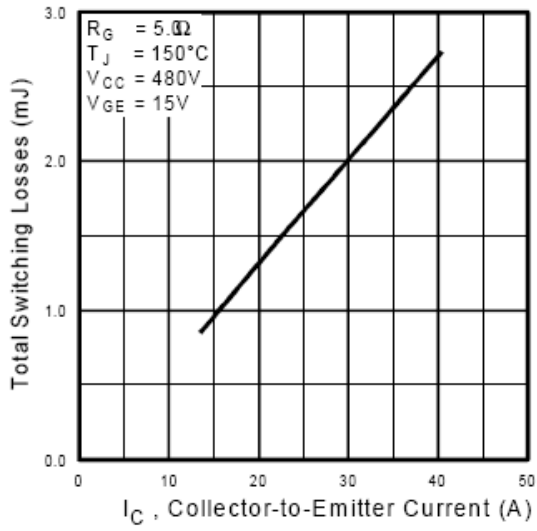
**Fig. 9** - Typical Switching Losses vs. Gate Resistance



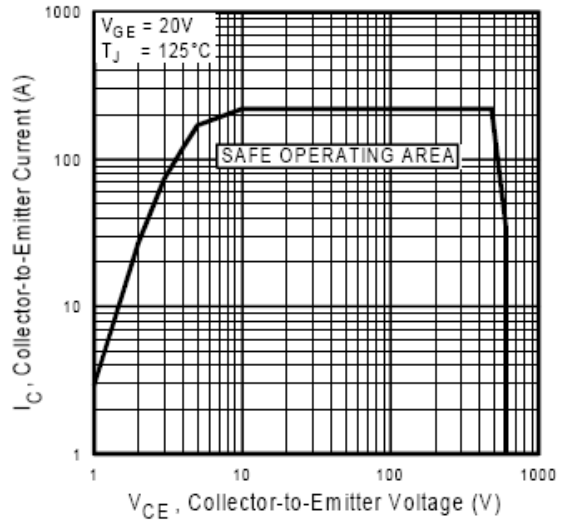
**Fig. 10** - Typical Switching Losses vs. Junction Temperature

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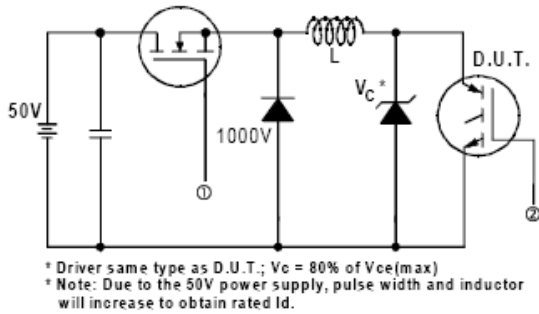
**Fig. 11** - Typical Switching Losses vs. Collector-to-Emitter Current



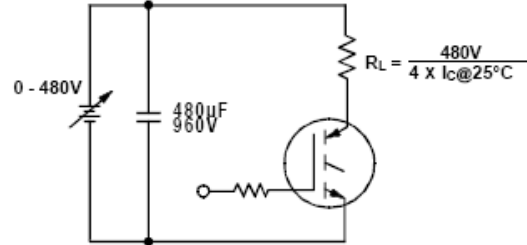
**Fig. 12** - Turn-Off SOA

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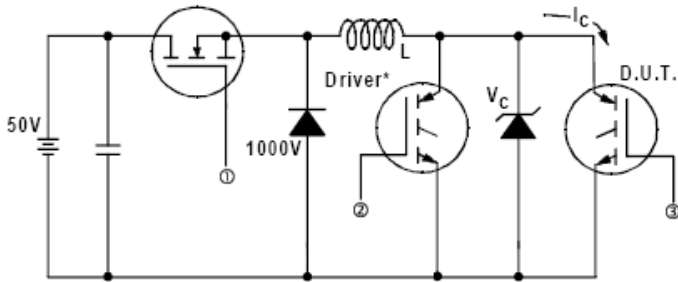
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**Fig. 13a** - Clamped Inductive Load Test Circuit

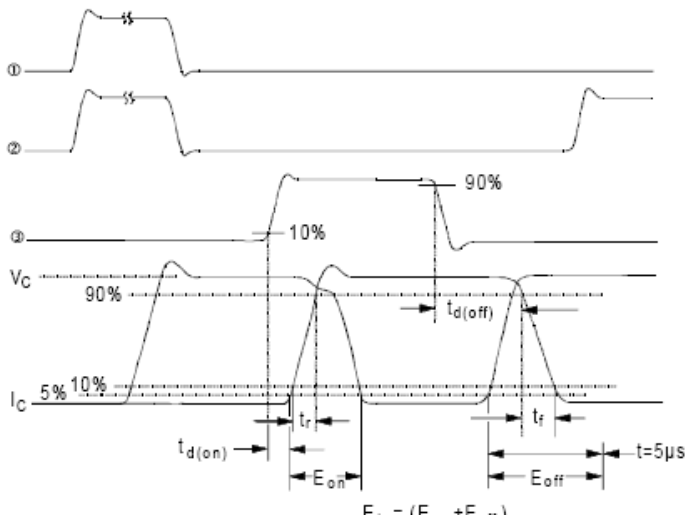


**Fig. 13b** - Pulsed Collector Current Test Circuit



**Fig. 14a** - Switching Loss Test Circuit

\* Driver same type as D.U.T.,  $V_C = 480V$



**Fig. 14b** - Switching Loss Waveforms